

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

# CPH3212 — NPN Epitaxial Planar Silicon Transistor DC / DC Converter Applications

## **Applications**

· Relay drivers, lamp drivers, motor drivers, flash

#### **Features**

- · Adoption of MBIT processes
- · High current capacitance
- · Low collector-to-emitter saturation voltage
- Ultrasmall package facilitates miniaturization in end products (mounting height: 0.9mm)
- · High allowable power dissipation

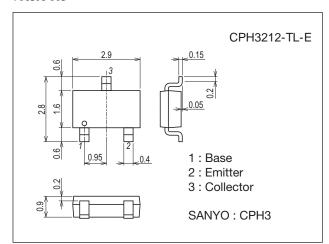
### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCES		100	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		5	Α
Collector Current (Pulse)	ICP		7	Α
Base Current	IB		1.2	Α
Collector Dissipation	PC	When mounted on ceramic substrate (600mm <sup>2</sup> ×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7015A-003



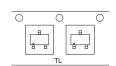
#### **Product & Package Information**

• Package : CPH3

• JEITA, JEDEC : SC-59, TO-236, SOT-23

• Minimum Packing Quantity : 3,000 pcs./reel

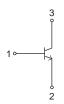
#### Packing Type: TL



# Marking



#### **Electrical Connection**



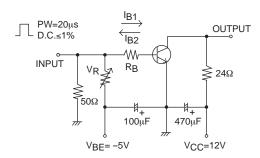
#### **SANYO Semiconductor Co., Ltd.**

http://semicon.sanyo.com/en/network

#### **Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Limit
		Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =40V, I <sub>E</sub> =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA	200		560	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA		330		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		26		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =2A, I <sub>B</sub> =40mA		100	150	mV
Base-to-Emitter Saturation Voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =2A, I <sub>B</sub> =40mA		0.80	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0A	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	IC=100μA, RBE=0Ω	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0A	6			V
Turn-On Time	ton			32		ns
Storage Time	tstg	See specified Test Circuit.		420		ns
Fall Time	tf			28		ns

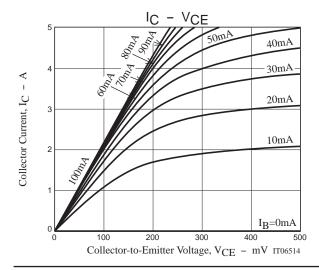
# **Switching Time Test Circuit**

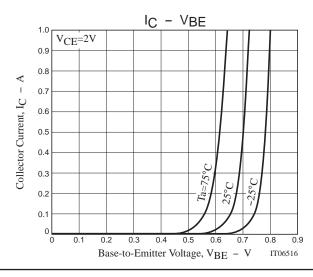


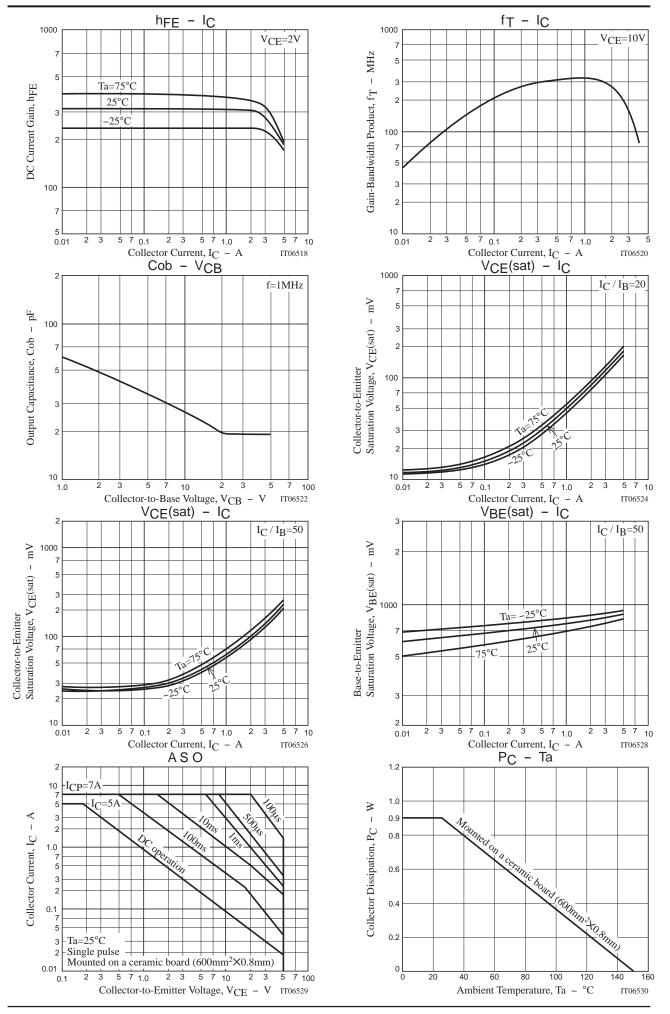
 $I_{C}=20I_{B1}=-20I_{B2}=2.5A$ 

# **Ordering Information**

Device	Package	Shipping	memo	
CPH3212-TL-E	CPH3	3,000pcs./reel	Pb Free	





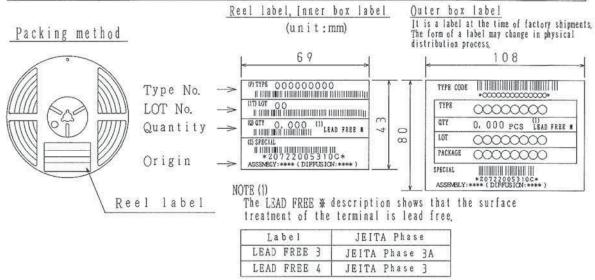


#### **Embossed Taping Specification**

#### CPH3212-TL-E

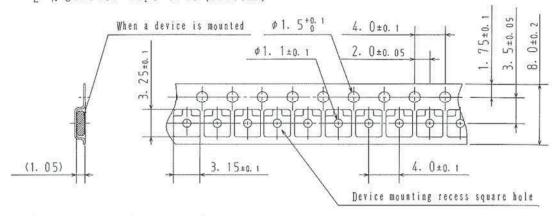
#### 1. Packing Format

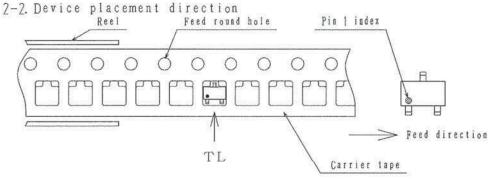
Package Name Ca	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Type	Reel	laner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
СРНЗ	СРНЗ	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210	



# 2. Taping configuration

#### 2-1. Carrier tape size (unit:mm)





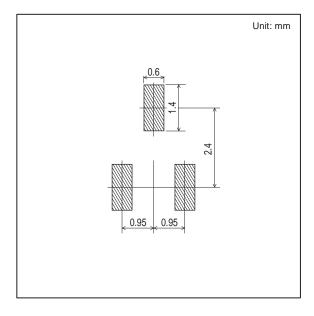
Those with one electrode terminal on the feed hole side.....TL

# **Outline Drawing**

CPH3212-TL-E

# Mass (g) Unit 0.013 \*For reference mm 0. 15<sup>+0. 1</sup><sub>-0. 05</sub> 2. 9±0. 1 0.6±0.1 A 0. 2±0. 1 [ \*1 ] [ \*1 ] 0. 05±0.05 1.6±0.1 [ \*1 ] 2 0.6±0.1 0.95 PIN#1 \*1:Lot indication

# **Land Pattern Example**



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